

ABSTRACT OF THE DISCLOSURE

A method for manufacturing vertical GaN light emitting diodes is provided. The method comprises the steps of:

5 forming a light emitting structure on a sapphire substrate, said light emitting structure including a first conductive GaN clad layer, an active layer and a second conductive GaN clad layer. The light emitting structure is divided into plural units so that the first conductive GaN clad layer of a

10 thickness of at least approximately 100Å remains. A conductive substrate is attached to the divided upper surface of the light emitting structures using a conductive adhesive layer. A lower surface of the sapphire substrate is irradiated by laser beam so that the sapphire substrate is removed from the unit

15 light emitting structures. First and second contacts are formed respectively on the surfaces of the first conductive clad layer and the conductive substrate. Finally, The resulting structure is cut into plural unit light emitting diodes.

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